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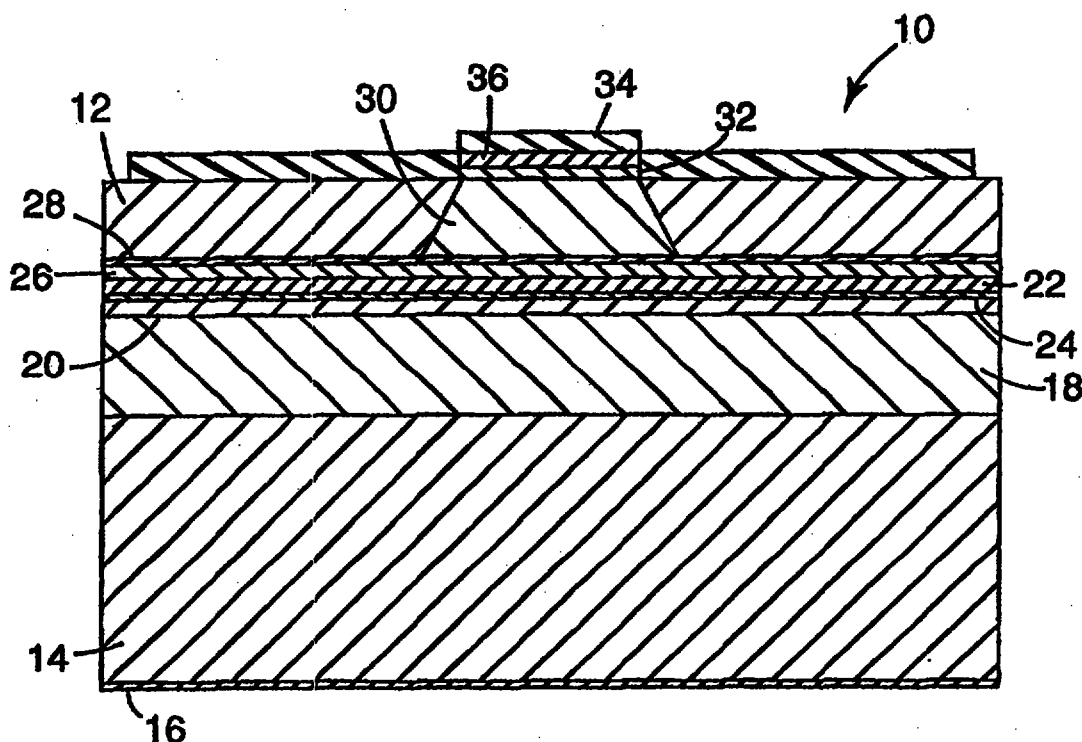
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(54) Title: SELECTIVE ETCH FOR II-VI SEMICONDUCTORS ✓



(57) Abstract

A II-VI semiconductor device is fabricated using a selective etchant in the form of aqueous solution of HX where X is Cl or Br. The II-VI semiconductor device is composed of a number of layers. Selective etching can be enabled by introducing Mg into one of the semiconductor layers. The resultant device may include a semiconductor layer containing Mg.